

### **IN THE SPECIFICATION**

**The paragraph starting on line 5 of page 7 should be amended as follows:**

Figure 2 is a planar view of an embodiment of a portion of an array 205 of field emitter devices including 250A, 250B, 205C,..., 250N, and constructed according to an embodiment of the present invention. The field emitter array ~~250~~ 205 includes a number of cathodes, 201<sub>1</sub>, 201<sub>2</sub>, 201<sub>3</sub>, ..., 201<sub>n</sub>, formed in rows along a substrate 200. A gate insulator 202 is formed along the substrate 200 and surrounds the cathodes. A number of gate lines are on the gate insulator. A number of anodes including 227<sub>1</sub>, 227<sub>2</sub>, 227<sub>3</sub>, ..., 227<sub>n</sub> are formed in columns orthogonal to and opposing the rows of cathodes. In one embodiment, the anodes include multiple phosphors. In another embodiment, the anodes are coated with a phosphorescent or luminescent substances or compounds. Additionally, the intersection of the rows and columns form pixels.

**The paragraph starting on line 15 of page 9 should be amended as follows:**

Figure 3G shows the structure after the next sequence of processing. Here a portion of the insulator layer 308 is removed from surrounding the cathode tip 301, leaving a gap 329 between elements of the gate layer 316. The portion of the insulator layer 308 is removed using any suitable technique as will be understood by one of ordinary skill in the field of semiconductor processing and field emission device fabrication. The formation of the anode 327 is further formed opposite the cathode tip 301 in order to complete the field emission device. The formation of the anode, and completion of the field emission device structure, can be achieved in numerous ways as will be understood by those of ordinary skill in the art of semiconductor and field emission device fabrication.

**The paragraph starting on line 24 of page 9 should be amended as follows:**

Figures 4A-4G show fabrication of a field emitter device according to an embodiment of the present invention. Figure 4A show the structure focusing on the cathode tip 401, having a width 425, after tip sharpening, following the first stages of processing. These stages are taught, for example, in Figures 1-5 in co-pending Application No. 09/261,477, entitled Structure and Method for Field Emitter Tips, filed February 26, 1999.